Optical Phonon R&D Or What Condensed Matter Theory/Computation Can do For You

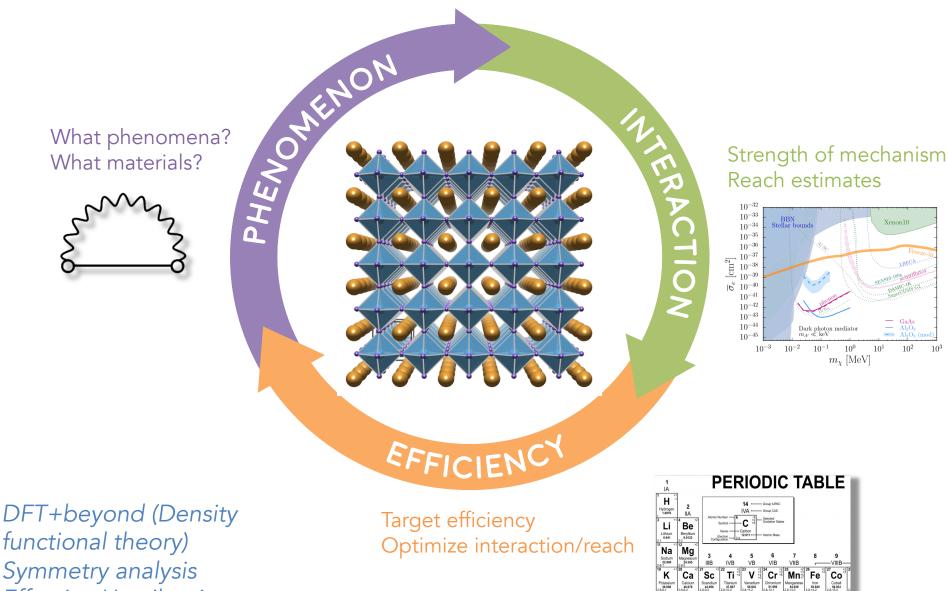


Light years



Nanometers

Target Theory and Design



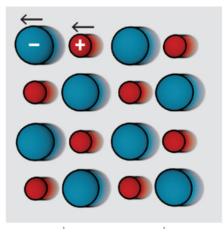
Titanium 47.867

<u>^{**}Sr^{**} Y ^{***}7r^{***}Nh³**Mn³**Tc [‡]**Ru^{**}*Rh^{**}</u>

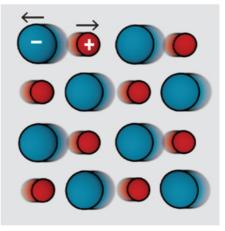
Effective Hamiltonians

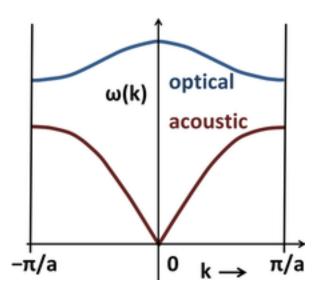
Phonons are Lattice Vibrations

Acoustic Phonons



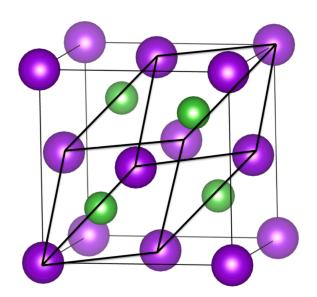
Optical Phonons





What are Polar Materials?

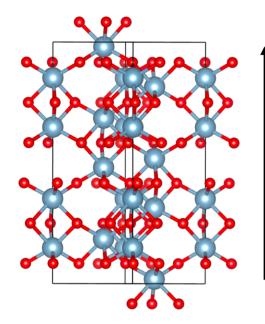
- At least two different ionic species
- Local dipole moment



GaAs

2 atoms in primitive cell

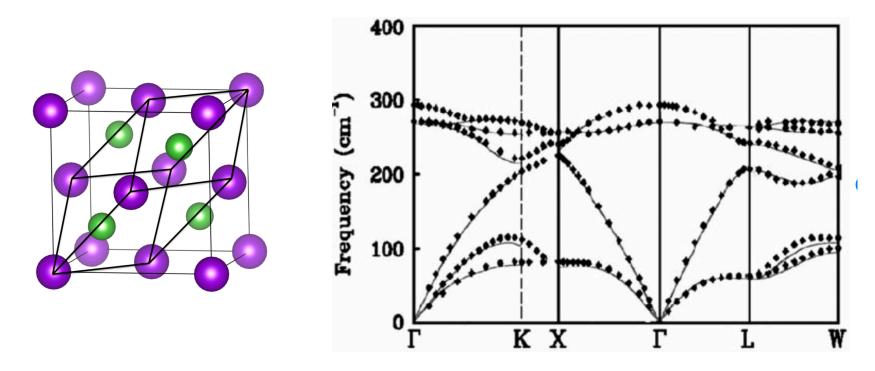
Al₂O₃ (Sapphire)



10 atoms in primitive cell

Primary crystal axis

Why Polar Materials?

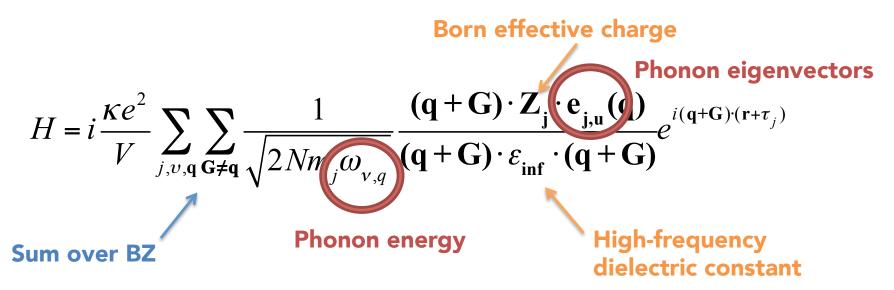


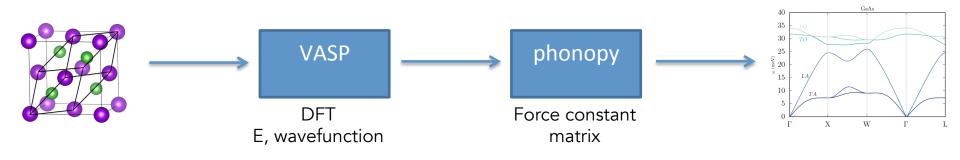
From Strauch & Dorner, JPCM 2 1457 (1990)

- 1. Kinematic matching with optical phonons
- 2. Small screening (insulating or semiconducting)
- 3. Can have anisotropic crystal structure (directional detection)
- 4. High-quality crystals available now

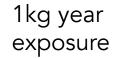
Discussing DM absorption via dark phonon with optical phonons

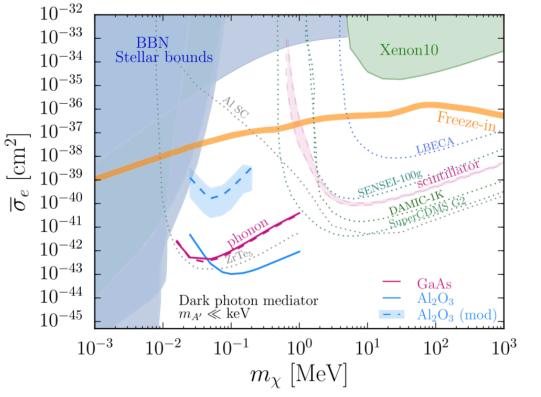
Fröhlich Hamiltonian – DM/phonon interaction





Theoretical reach of optical phonons





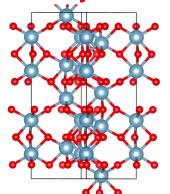


Tongyan Lin, UCSD

Simon Knapen, IAS

Kathryn Zurek, LBL

Hidden bonus: directionality!



Primary crystal axis

$$Q = \frac{Z^{*^2}}{A_1 A_2 \varepsilon_{\infty}^2 \omega_{LO}}$$

Z*= Born effective charges A_1, A_2 = atomic mass numbers ε_{inf} = high-frequency dielectric constant w_{LO} = optical phonon frequency

	Ζ*	A ₁	A ₂	Eps_inf	w _{LO} (meV)	Q (E-7)
GaAs	2.27	69.7	74.9	10.89 (14.8)	25, 35	2.4
Al ₂ O ₃	2.98, 1.34	27.0	16.0	3.3	30, 106	80

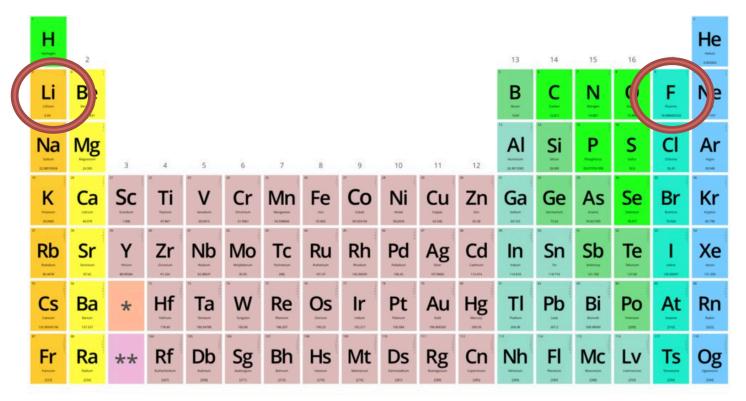


Kevin Zhang, LBL Tanner Trickle, LBL Kathryn Zurek, LBL

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 $\begin{aligned} \mathbf{Z^{*=} Born effective charges} \\ \mathbf{A_{1}, A_{2}=} atomic mass numbers} \\ \epsilon_{inf} = high-frequency dielectric constant} \\ \mathbf{w_{LO}} = optical phonon frequency \end{aligned}$

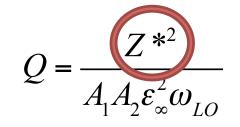




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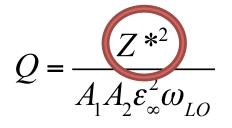
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LiF	1.05	6.9	19.0	2.02	77	268



Z*= Born effective charges A_1, A_2 = atomic mass numbers ε_{inf} = high-frequency dielectric constant w_{LO} = optical phonon frequency

$$Z^* = \frac{V}{e} \frac{\partial P}{\partial u}$$

Materials with large electric polarization?



Z*= Born effective charges A_1, A_2 = atomic mass numbers ε_{inf} = high-frequency dielectric constant w_{LO} = optical phonon frequency

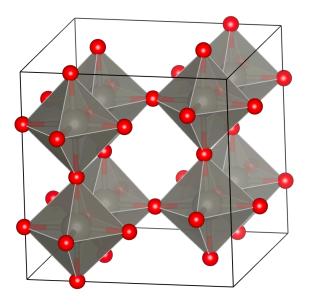
$$Z^* = \frac{V}{e} \frac{\partial P}{\partial u}$$

Materials with large electric polarization?

WO₃ (in P4mm structure)

Calculated polarization of **69 µC.cm⁻²** (high)

Hamdi et al. PRB 94, 245124 (2016)



$$Q = \frac{Z^{*2}}{A_1 A_2 \varepsilon_{\infty}^2 \omega_{LO}}$$

Z*= Born effective charges A₁, A₂= atomic mass numbers ε_{inf} = high-frequency dielectric constant \mathbf{w}_{LO} = optical phonon frequency

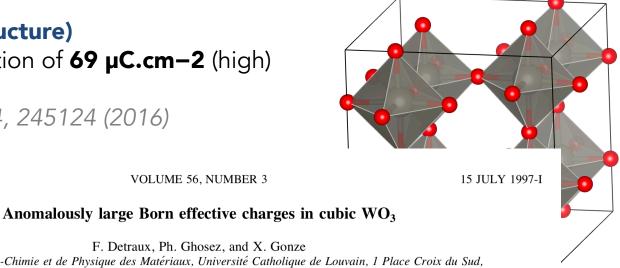
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Hamdi et al. PRB 94, 245124 (2016)

PHYSICAL REVIEW B



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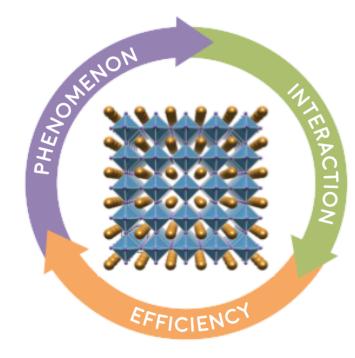
(Received 15 January 1997)

$$Q = \frac{Z^{*^2}}{A_1 A_2 \sum_{\infty}^2 \omega_{LO}}$$

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Al ₂ O ₃	2.98, 1.34	27.0	16.0	3.3	30, 106	80
LiF	1.05	6.9	19.0	2.02	77	268
WO ₃	11.73, 8.78, 1.62	183.8	16.0	5	126	556

Optical Phonon Theory and Design – Future



Multi-phonon production

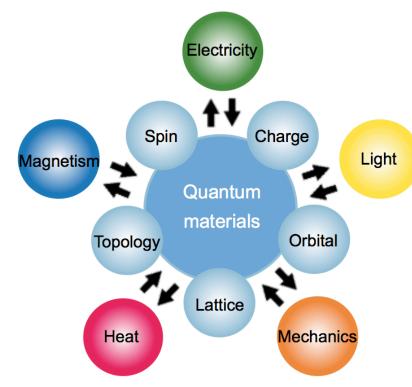
Lin, Knapen Harrelson, Trickle, Zhang, Zurek

Phonon lifetimes Harrelson

Better polar semiconductors

Theory and experiment

Ferroelectrics Lin, Knapen





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Characterization		Fabrication	Theory	Synthesis		
NCEM National Center for Electron Microscopy	Floor 1 Imaging and Manipulation of Nano- structures	Floor 2 Nano- fabrication	Floor 3 Theory of Nano- structured Materials	Floor 4 Inorganic Nano- structures	Floor 5 Biological Nano- structures	Floor 6 Organic and Macro- molecular Synthesis
Electron microscopy and nano- characterization	Characterization and manipulation of nanostructures	Advanced lithographic and thin-film processing techniques	Guiding understanding of new principles, behavior and experiments	Science of semiconductor, carbon and hybrid nanostructures	Bio-materials; new probes for bio-imaging; synthetic biology techniques	Soft materials: organics, macromolecules, polymers and their assemblies